

RGTH40TK65

650V 20A Field Stop Trench IGBT

V _{CES}	650V
I _{C(100°C)}	14A
V _{CE(sat) (Typ.)}	1.6V@I _C =20A
P_D	56W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

Applications

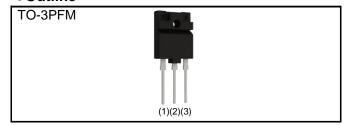
PFC

UPS

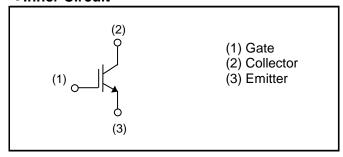
Power Conditioner

ΙH

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Type	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTH40TK65

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	23	А
	T _C = 100°C	I _C	14	А
Pulsed Collector Current		I _{CP} *1	80	А
Power Dissipation	T _C = 25°C	P _D	56	W
	T _C = 100°C	P _D	28	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{jmax.}

●Thermal Resistance

Doromotor	Symbol	Values			Unit
Parameter		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	2.64	°C/W

ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Uniii
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	1	-	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	ı	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, \ V_{CE} = 0V$	ı	ı	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 13.3 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 20A$, $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.6 2.1	2.1	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Cymbol	Conditions	Values			Unit
Parameter	Symbol		Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1060	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	47	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	18	-	
Total Gate Charge	Q _g	V _{CE} = 300V	-	40	-	
Gate - Emitter Charge	Q_{ge}	I _C = 20A	-	9	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	15	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 20A, V_{CC} = 400V$	-	22	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	25	-	20
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	73	-	ns
Fall Time	t _f	Inductive Load	-	48	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 20A, V_{CC} = 400V$	-	22	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	25	-	20
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	83	-	ns
Fall Time	t _f	Inductive Load	-	58	-	
		$I_C = 80A, V_{CC} = 520V$				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FU	FULL SQUARE		
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

Fig.1 Power Dissipation vs. Case Temperature

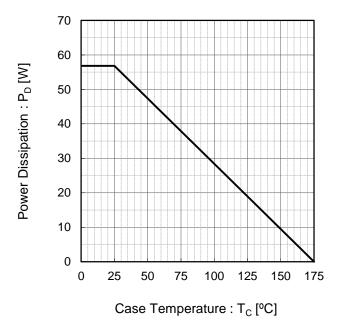


Fig.2 Collector Current vs. Case Temperature

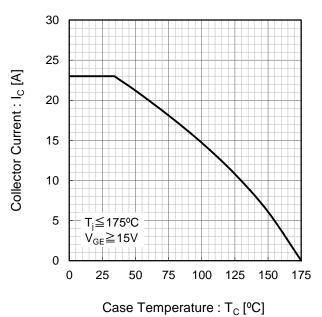


Fig.3 Forward Bias Safe Operating Area

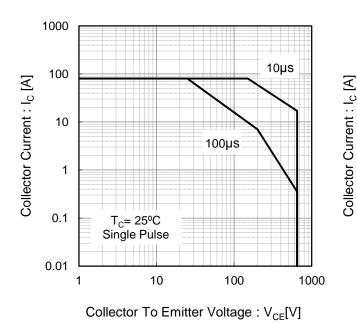
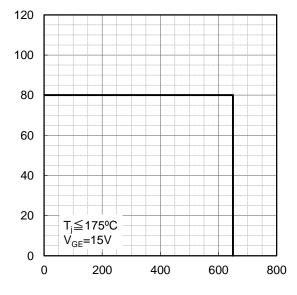


Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage : $V_{CE}[V]$

Fig.5 Typical Output Characteristics

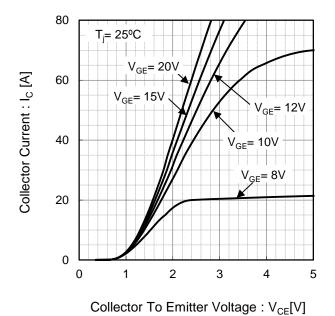
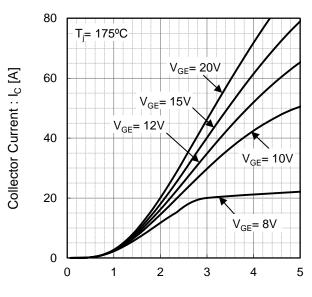


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V_{CE}[V]

Fig.7 Typical Transfer Characteristics

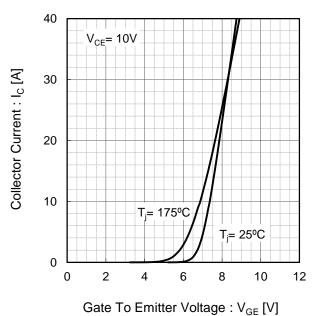
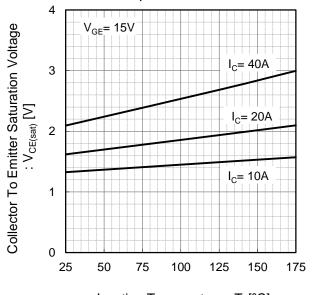
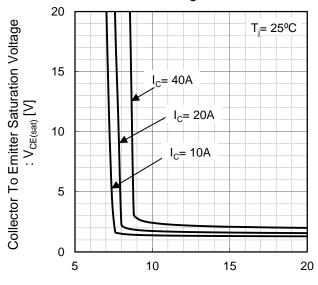


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



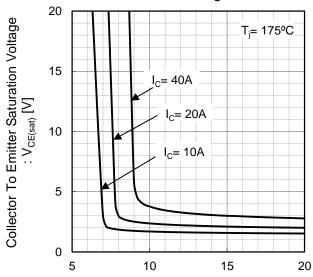
Junction Temperature : T_i [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V_{GE} [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage: V_{GE} [V]

Fig.11 Typical Switching Time vs. Collector Current

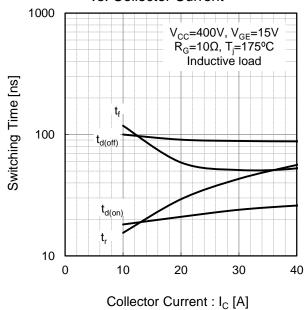


Fig.12 Typical Switching Time vs. Gate Resistance

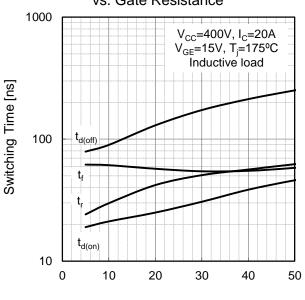


Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ 0.1 V_{CC} =400V, V_{GE} =15V R_{G} =10 Ω , T_{j} =175°C Inductive load 0.01 0 10 30 20 40 Collector Current : I_C [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ Eor 0.1 V_{CC}=400V, I_C=20A V_{GE}=15V, T_j=175°C Inductive load 0.01 10 40 0 20 30 50 Gate Resistance : $R_G[\Omega]$

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] 100 Coes Cres 10 f=1MHz $V_{GE}=0V$ T_i=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V_{CE}[V]

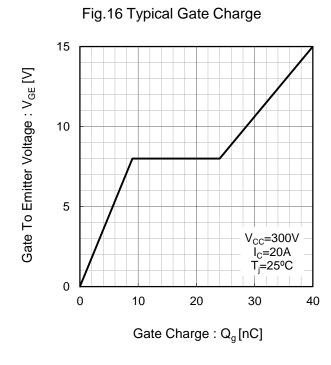
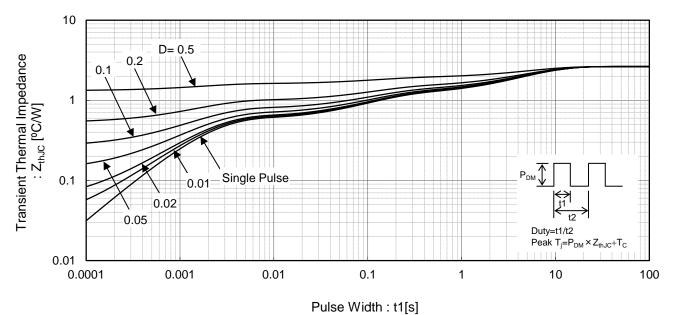


Fig.17 IGBT Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

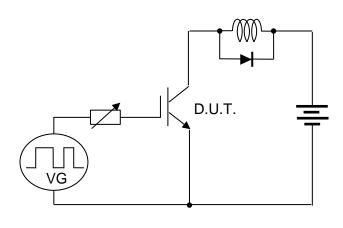


Fig.18 Inductive Load Circuit

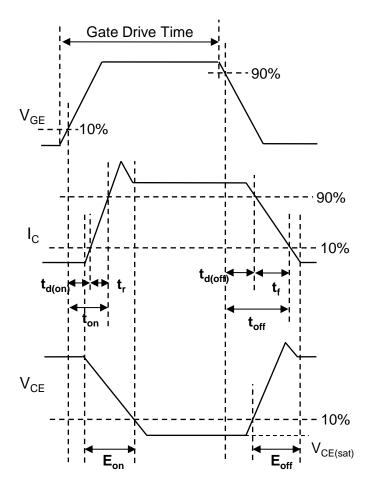


Fig.19 Inductive Load Waveform

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 IKFW50N65ES5XKSA1
 IKFW50N65EH5XKSA1
 IKFW40N65ES5XKSA1

 IKFW60N65ES5XKSA1
 IMBG120R090M1HXTMA1
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 IHW20N65R5XKSA1
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